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MICROWAVE CORPORATION v04.0414



HMC460LC5

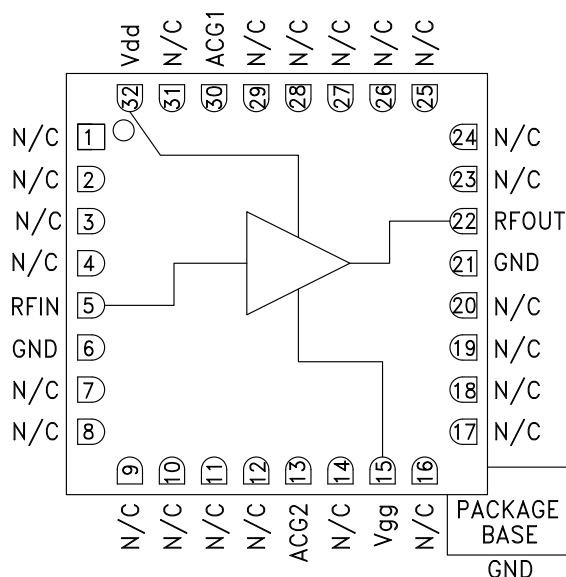
GaAs pHEMT MMIC LOW NOISE AMPLIFIER, DC - 20 GHz

Typical Applications

The HMC460LC5 is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military & Space
- Test Instrumentation

Functional Diagram



Features

Noise Figure: 2.5 dB @ 10 GHz

Gain: 14 dB @ 10 GHz

P1dB Output Power: +16.5 dBm @ 10 GHz

Supply Voltage: +8V @ 75 mA

50 Ohm Matched Input/Output

32 Lead Ceramic 5x5mm SMT Package: 25mm²

General Description

The HMC460LC5 is a GaAs MMIC pHEMT Low Noise Distributed Amplifier in a leadless 5x5 mm ceramic surface mount package which operates from DC to 20 GHz. The amplifier provides 14 dB of gain, 2.5 dB noise figure and +16.5 dBm of output power at 1 dB gain compression while requiring only 75 mA from a Vdd = 8V supply. Gain flatness is excellent from DC to 20 GHz making the HMC460LC5 ideal for EW, ECM, Radar and test equipment applications. The wideband amplifier I/Os are internally matched to 50 Ohms.

Electrical Specifications, $T_A = +25^\circ\text{C}$, Vdd= 8V, Idd= 75 mA*

Parameter	Min.	Typ.	Max.	Min.	Typ.	Max.	Min.	Typ.	Max.	Units
Frequency Range		DC - 6.0		6.0 - 18.0			18.0 - 20.0			GHz
Gain	11	14		11	14		10	13		dB
Gain Flatness		± 0.5			± 0.15			± 0.25		dB
Gain Variation Over Temperature		0.008			0.01			0.01		dB/°C
Noise Figure		3.5	5.0		2.5	4.0		3.5	5	dB
Input Return Loss		17			18			12		dB
Output Return Loss		17			15			15		dB
Output Power for 1 dB Compression (P1dB)	14	17		13	16		12	15		dBm
Saturated Output Power (Psat)		18			18			17		dBm
Output Third Order Intercept (IP3)		29.5			29			28.5		dBm
Supply Current (Idd) (Vdd= 8V, Vgg= -0.9V Typ.)		75			75			75		mA

* Adjust Vgg between -2 to 0V to achieve Idd= 75 mA typical.

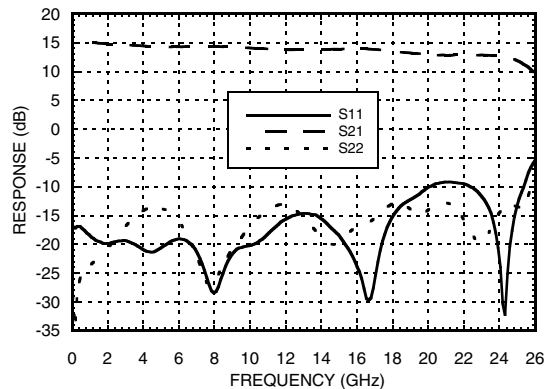
For price, delivery and to place orders: Hittite Microwave Corporation, 2 Elizabeth Drive, Chelmsford, MA 01824

Phone: 978-250-3343 Fax: 978-250-3373 Order On-line at www.hittite.com

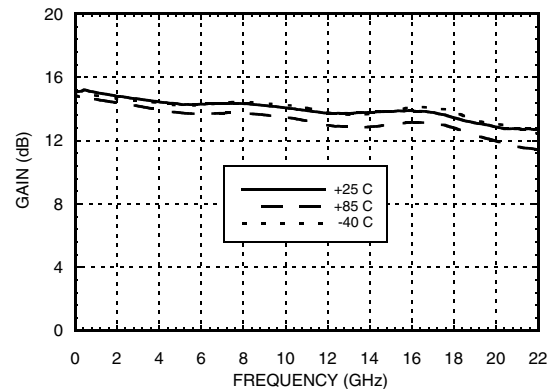
Application Support: Phone: 978-250-3343 or apps@hittite.com

GaAs pHEMT MMIC LOW NOISE AMPLIFIER, DC - 20 GHz

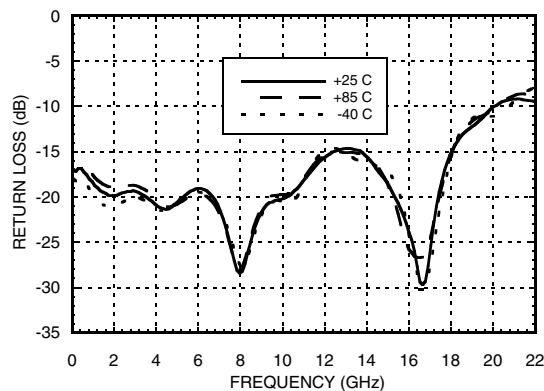
Broadband Gain & Return Loss



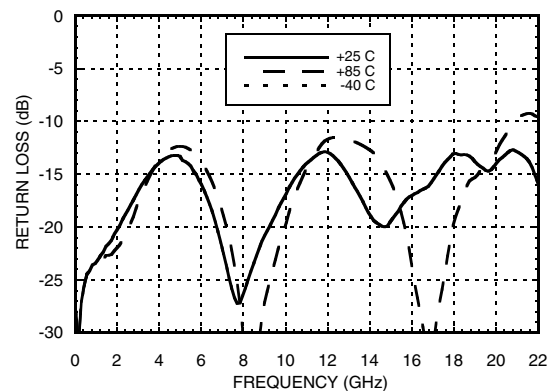
Gain vs. Temperature



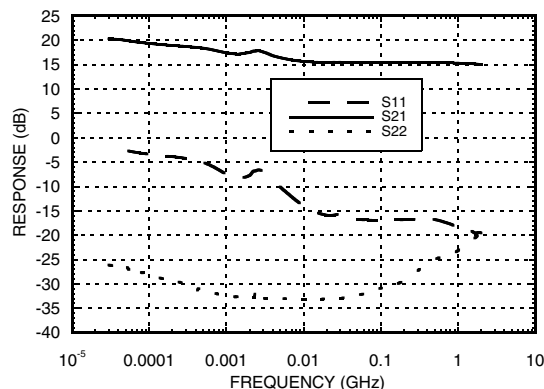
Input Return Loss vs. Temperature



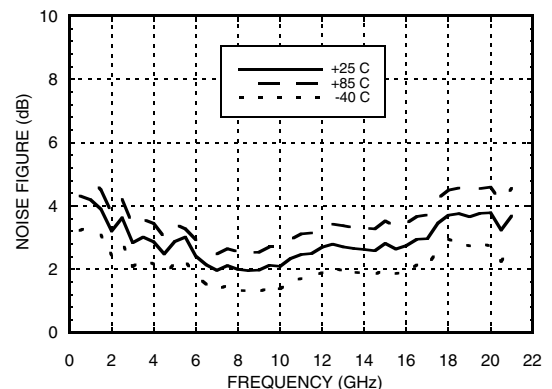
Output Return Loss vs. Temperature



Low Frequency Gain & Return Loss



Noise Figure vs. Temperature





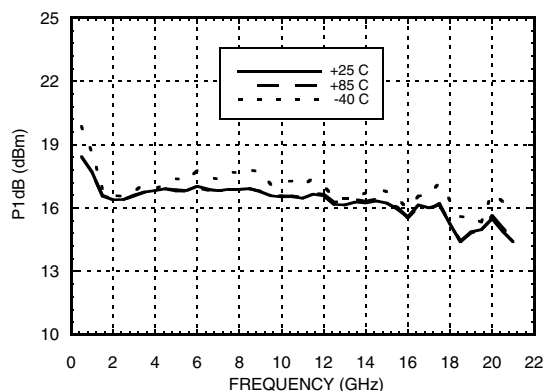
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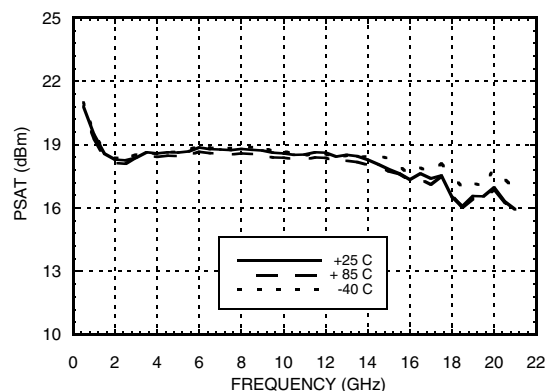
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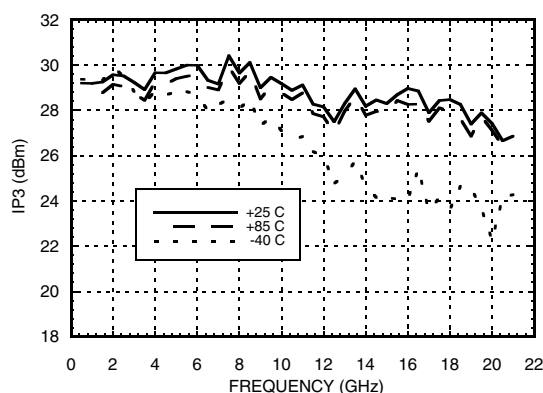
P1dB vs. Temperature



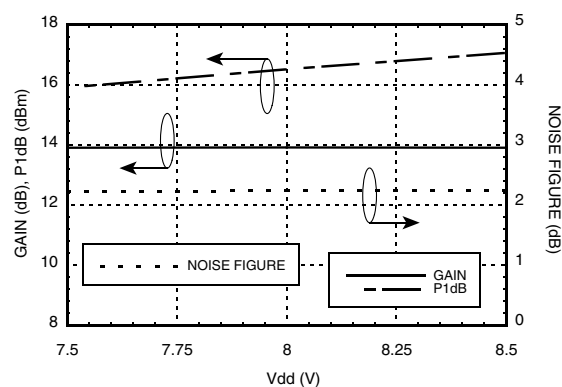
Psat vs. Temperature



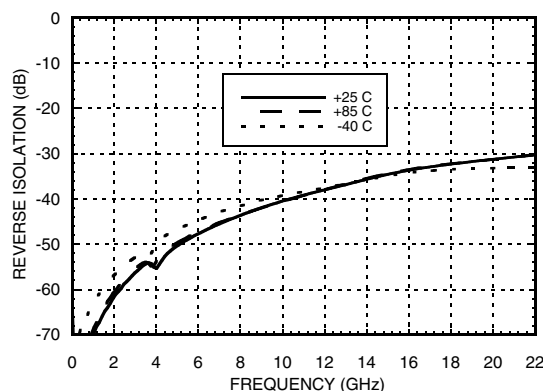
Output IP3 vs. Temperature



Gain, Power & Noise Figure vs. Supply Voltage @ 10 GHz, Fixed Vgg



Reverse Isolation vs. Temperature



**GaAs pHEMT MMIC LOW NOISE
AMPLIFIER, DC - 20 GHz**
Absolute Maximum Ratings

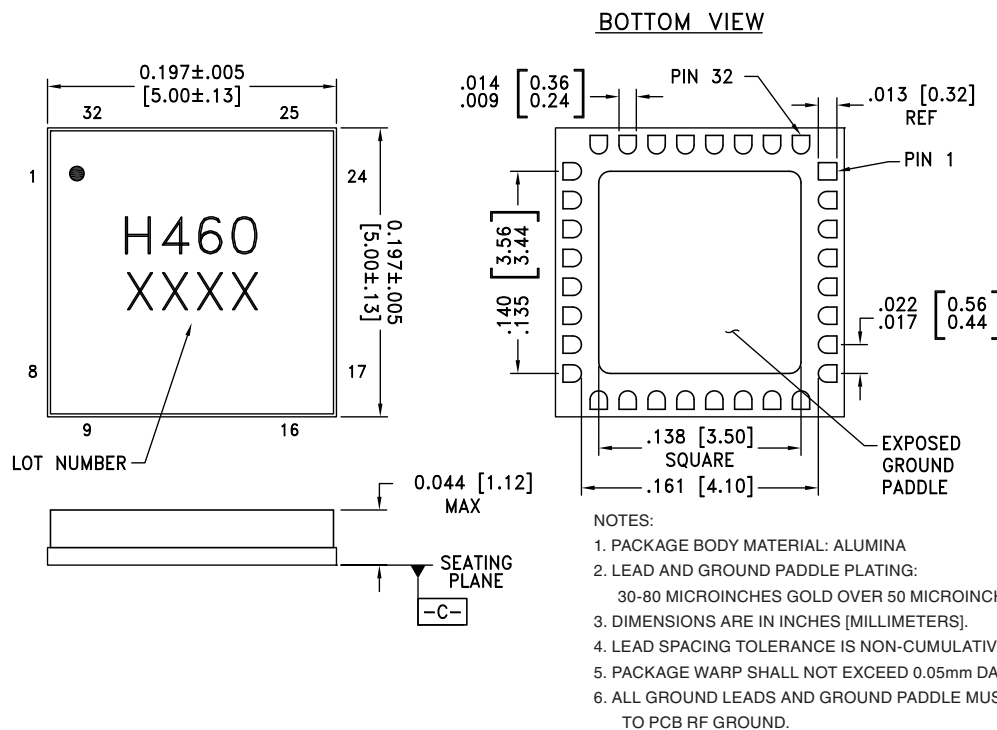
Drain Bias Voltage (Vdd)	+9 Vdc
Gate Bias Voltage (Vgg)	-2 to 0 Vdc
Gate Bias Voltage (Igg)	2.5 mA
RF Input Power (RFIN)(Vdd = +8 Vdc)	+18 dBm
Channel Temperature	175 °C
Continuous P _{diss} (T = 85 °C) (derate 23 mW/°C above 85 °C)	2 W
Thermal Resistance (channel to package bottom)	44.4 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C

Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
+7.5	74
+8.0	75
+8.5	76



**ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS**

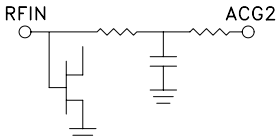
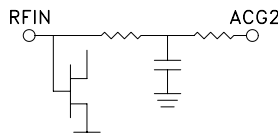
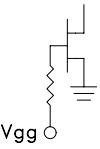
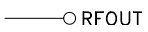
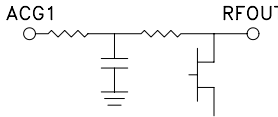
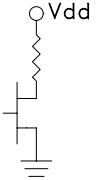
Outline Drawing

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[2]
HMC460LC5	Alumina, White	Gold over Nickel	MSL3 ^[1]	H460 XXXX

[1] Max peak reflow temperature of 260 °C

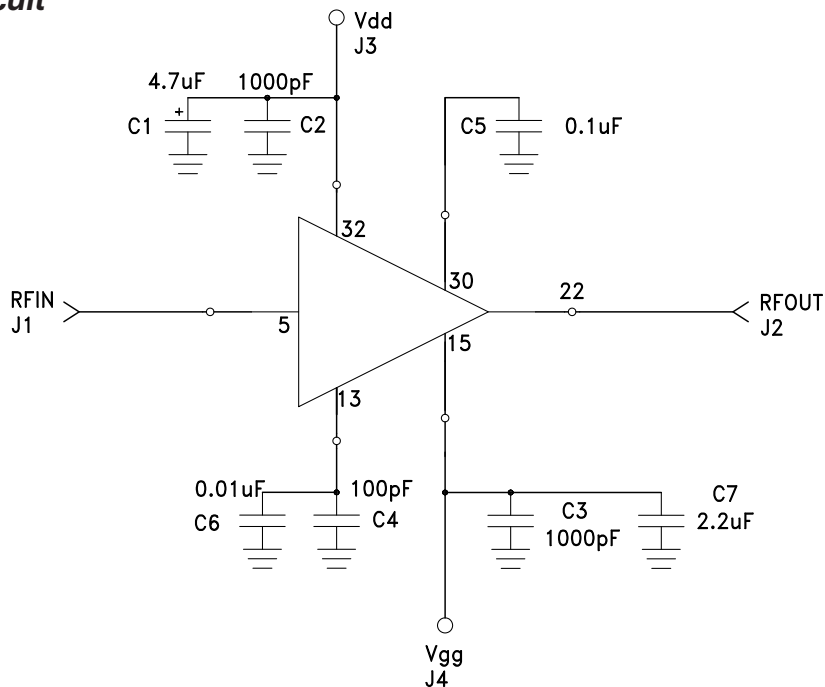
[2] 4-Digit lot number XXXX

Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1 - 4, 7 - 12, 14, 16 - 20, 23 - 29, 31	N/C	No connection. These pins may be connected to RF ground. Performance will not be affected.	
5	RFIN	This pin is DC coupled and matched to 50 Ohms.	
6, 21	GND	Package bottom must be connected to RF/DC ground.	
13	ACG2	Low frequency termination. Attach bypass capacitor per application circuit herein.	
15	Vgg	Gate control for amplifier. Please follow "MMIC Amplifier Biasing Procedure" application note	
22	RFOUT	This pin is DC coupled and matched to 50 Ohms.	
30	ACG1	Low frequency termination. Attach bypass capacitor per application circuit herein.	
32	Vdd	Power supply voltage for the amplifier. External bypass capacitors are required	

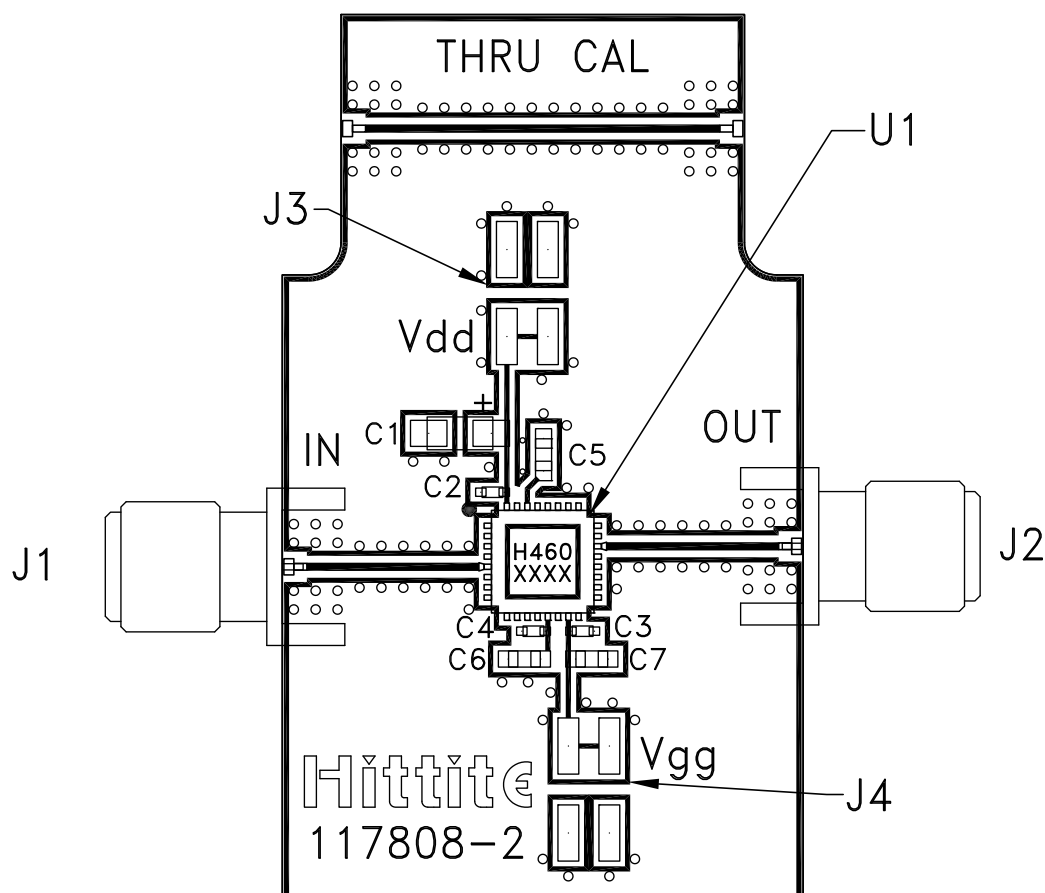
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Application Circuit



GaAs pHEMT MMIC LOW NOISE AMPLIFIER, DC - 20 GHz

Evaluation PCB



List of Materials for Evaluation PCB 117810 [1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3 - J4	2 mm Molex Header
C4	100 pF Capacitor, 0402 Pkg.
C2, C3	1000 pF Capacitor, 0402 Pkg.
C1	4.7 μ F Capacitor, Tantalum
C5	0.1 μ F Capacitor, 0603 Pkg.
C6	0.01 μ F Capacitor, 0603 Pkg.
C7	2.2 μ F Capacitor, 0603 Pkg.
U1	HMC460LC5
PCB [2]	117808 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.



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**GaAs pHEMT MMIC LOW NOISE
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AMPLIFIERS - LOW NOISE - SMT